

Ab initio Studies of 1-photon and Coherent 2-photon Photoemission on Cs₃Sb and GaAs

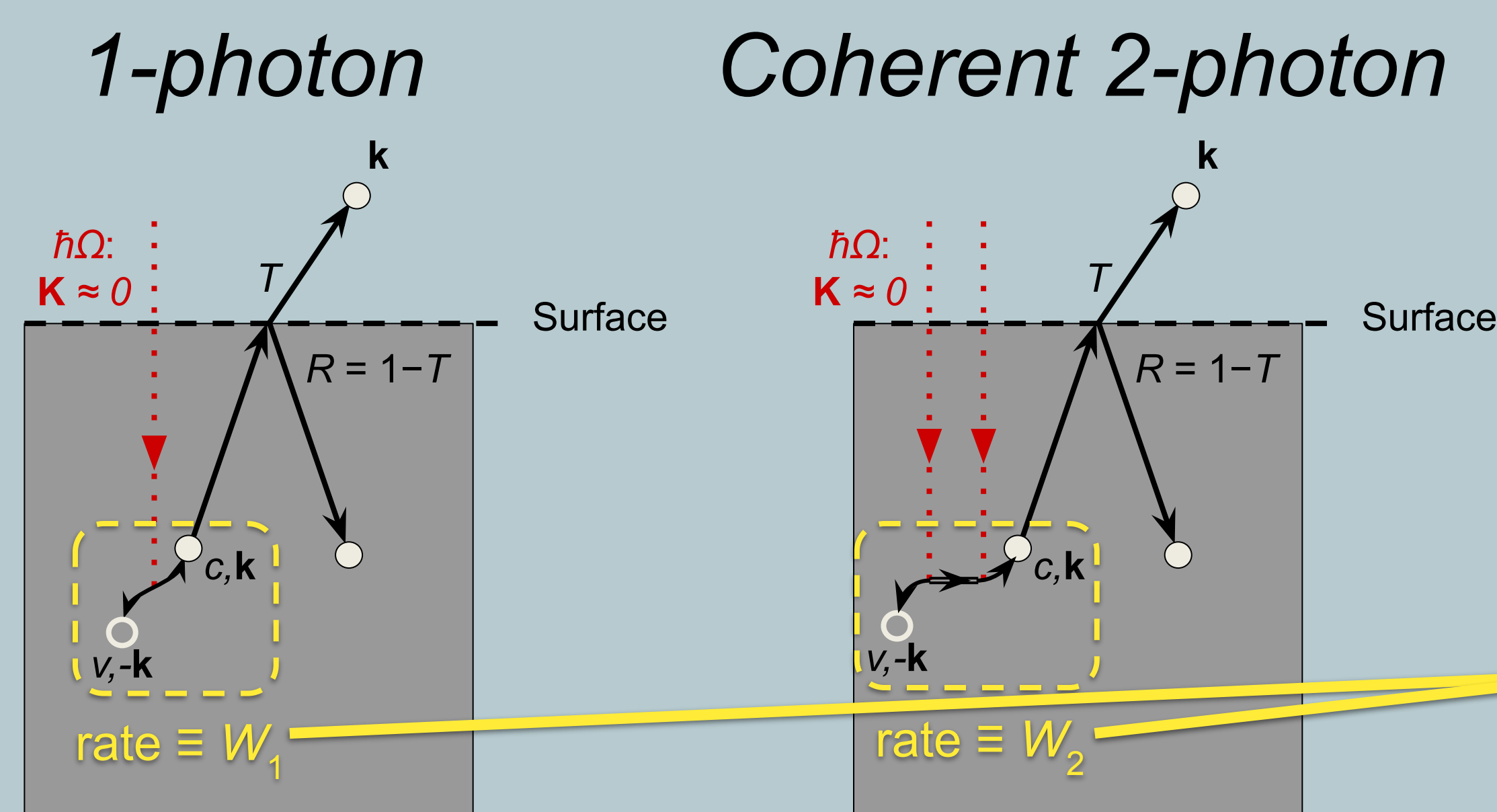
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Ab initio Photoemission Calculations

Bulk processes studied since more bulk e⁻ than surface e⁻

- Photon(s) excite e⁻-h⁺ pair in 2 ways:
 - 1-photon excitation
 - Coherent 2-photon excitation
- Coherent outgoing scattering state
 - $E_{\perp} > 0 \Rightarrow$ use $T = 100\%$
 - $E_{\perp} \leq 0 \Rightarrow T = 0$



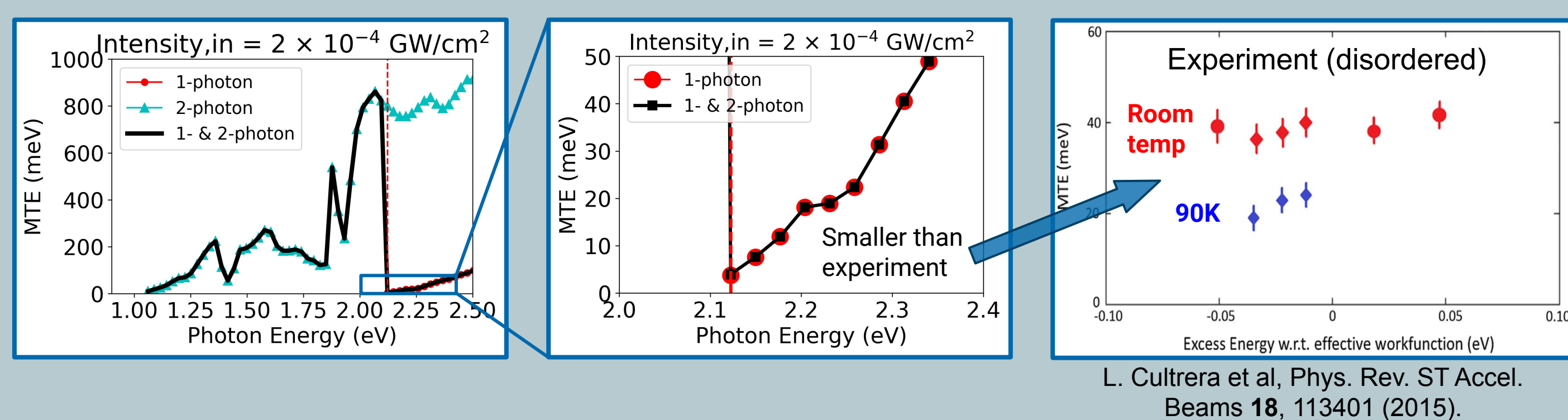
Use **absorption coefficient** α to compare numbers of excited electrons

$$\alpha_n = \frac{n\hbar\omega}{I_{in}} W_n$$

- $n = 1$ (1-photon) or 2 (coherent 2-photon)
- I_{in} = laser intensity inside material
- W_n = transition rate of process n

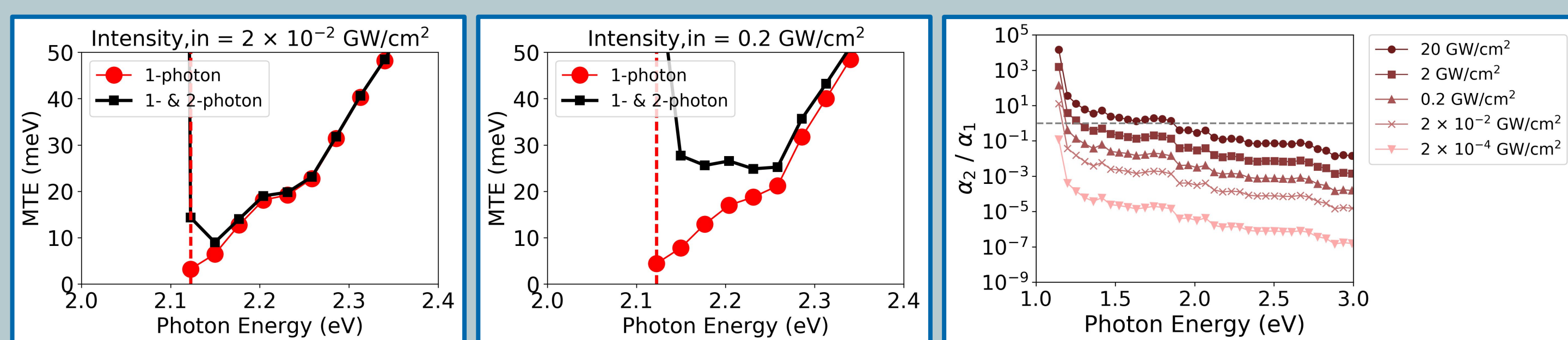
Results: Ideal Cs₃Sb(100)

- MTE at low laser intensity inside material (1-photon dominates)



L. Cultrera et al, Phys. Rev. ST Accel. Beams 18, 113401 (2015).

- Estimated 2-photon effects at higher laser intensities

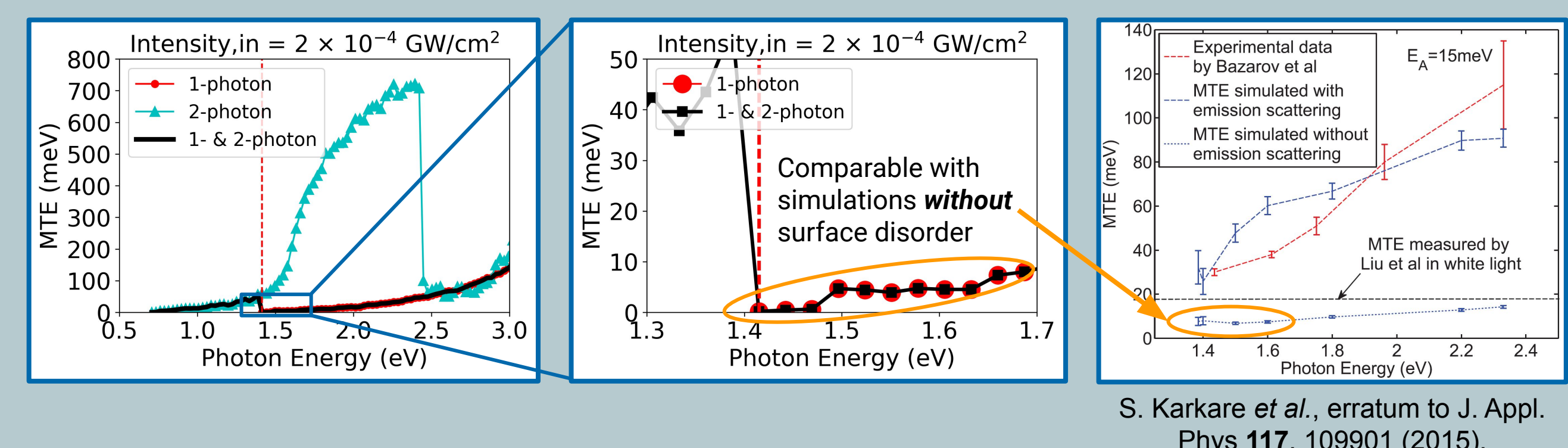


Estimated W_2 by scaling $\text{Im} \sum_{e\text{-phon}}$ to what they should be

- $W_2 \propto 1/\eta$; $\eta \equiv \text{Im} \sum_{e\text{-e}} + \text{Im} \sum_{e\text{-phon}} \approx \text{Im} \sum_{e\text{-phon}}$ ($\sim 10^4 \times \text{Im} \sum_{e\text{-e}}$)
- $\text{Im} \sum_{e\text{-phon}}$ too large; see "Cs₃Sb Re-relaxed Structure"

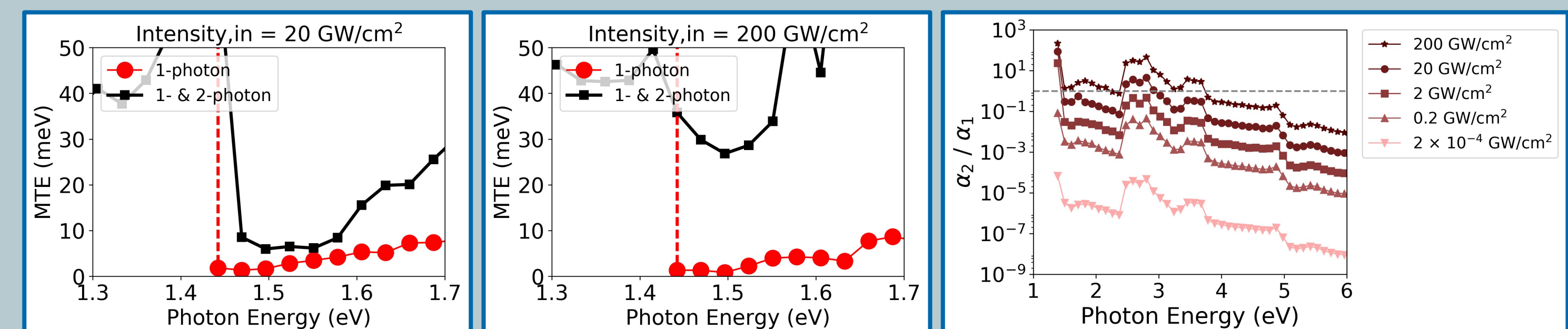
Results: Ideal GaAs(100) with $E_A = -0.02$ eV

- MTE at low laser intensity inside material (1-photon dominates)



S. Karkare et al., erratum to J. Appl. Phys 117, 109901 (2015).

- 2-photon effects at higher laser intensities

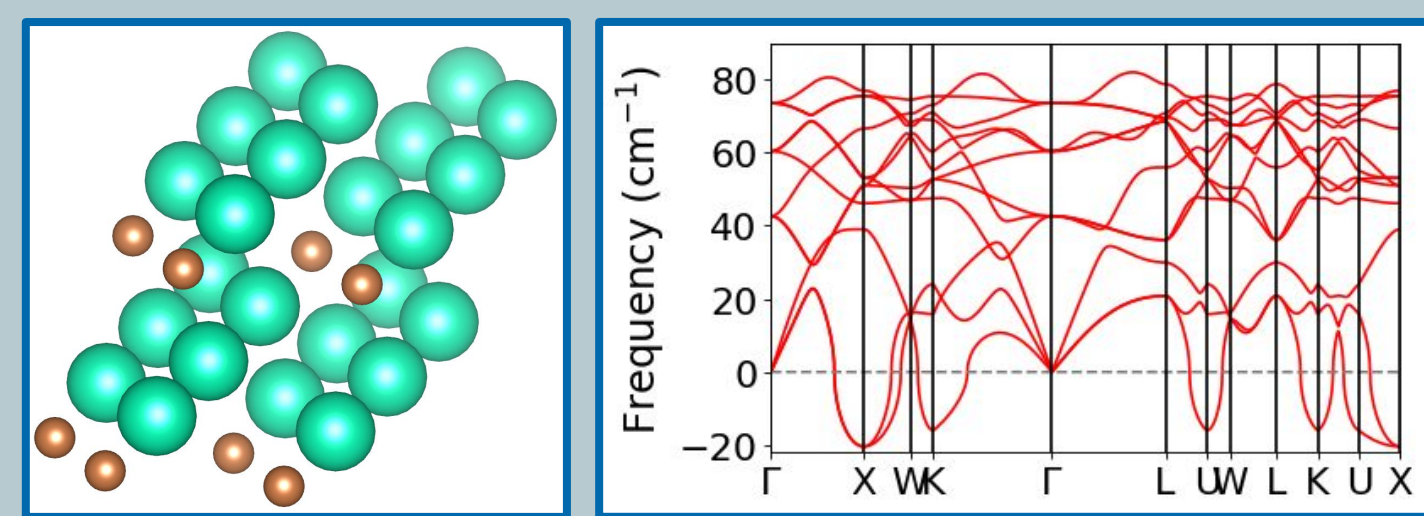


- Future work:

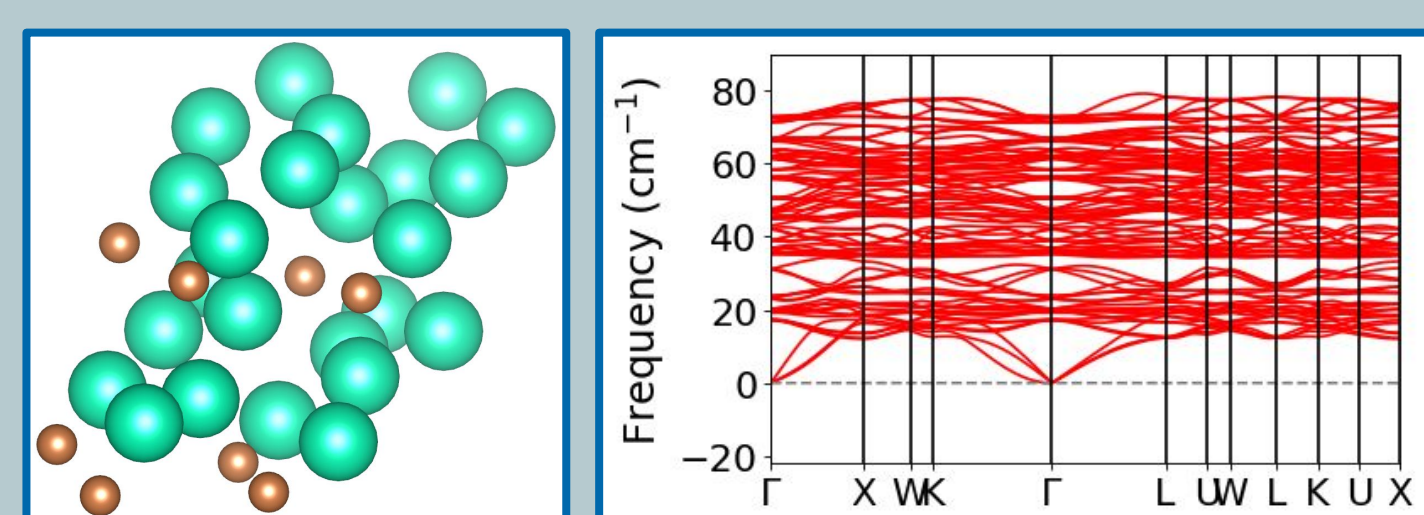
- Integrate to ultrafast-electron-heating Monte Carlo code (see O. Chubenko's and J. K. Bae's posters)

Cs₃Sb Re-relaxed Structure

- Commonly-used structure is **not** actual ground state



Commonly-used structure has *imaginary phonon frequencies*

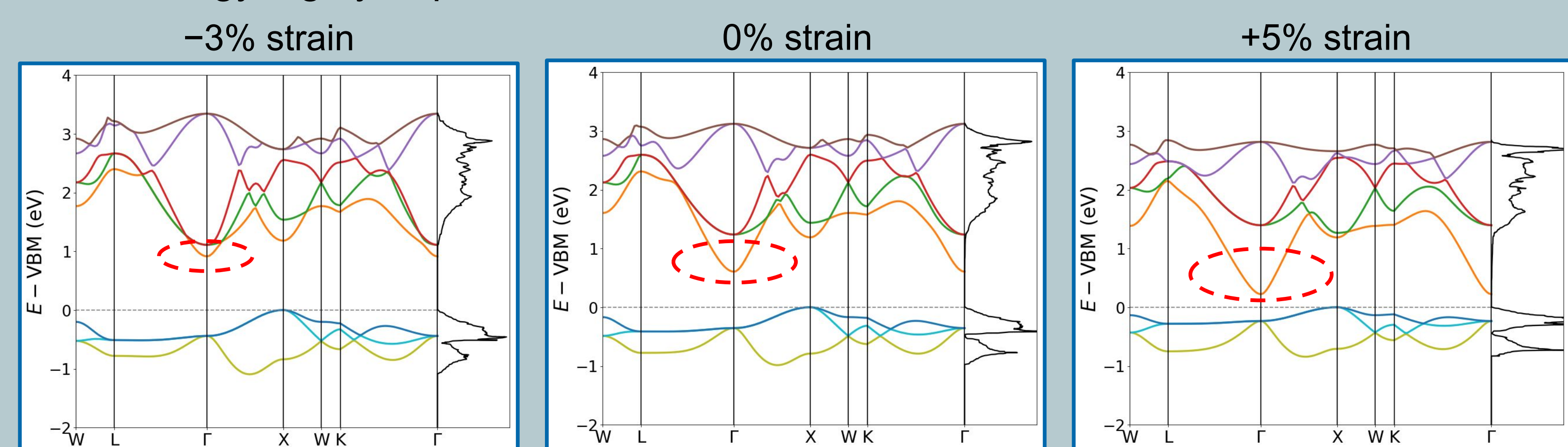


Re-relaxed structure using $2 \times 2 \times 2$ primitive FCC unit cell

- New $\text{Im} \sum_{e\text{-phon}} \sim 0.01 \times$ old $\text{Im} \sum_{e\text{-phon}}$ ($\sim 100 \times \text{Im} \sum_{e\text{-e}}$)
- Future work: Re-calculate MTE etc. for Cs₃Sb(100) using this re-relaxed, **stable** structure

"Mid-gap states" in Ideal Cs₃Sb

- Preliminary studies show band in gap with very low DOS
 - Energy highly depends on lattice constant / uniform strain



- Future work: effects of oxygen defects* and epitaxial strains
*XPS measurements suggest prevalence of oxides (W. DeBenedetti and M. A. Hines)